# MXXIM

# FOLLOWS DATA SHEET **High-Speed Step-Down Controller with** Synchronous Rectification for CPU Power

### **General Description**

The MAX1639 is an ultra-high-performance, step-down DC-DC controller for CPU power in high-end computer systems. Designed for demanding applications in which output voltage precision and good transient response are critical for proper operation, it delivers over 35A from 1.1V to 4.5V with  $\pm 1\%$  total accuracy from a +5V  $\pm 10\%$  supply. Excellent dynamic response corrects output transients caused by the latest dynamically clocked CPUs. This controller achieves over 90% efficiency by using synchronous rectification. Flying-capacitor bootstrap circuitry drives inexpensive, external N-channel MOSFETs.

The switching frequency is pin-selectable for 300kHz, 600kHz, or 1MHz. High switching frequencies allow the use of a small surface-mount inductor and decrease output filter capacitor requirements, reducing board area and system cost.

Output overvoltage protection is enforced by a crowbar circuit that turns on the low-side MOSFET with 100% duty factor when the output is 200mV above the normal regulation point. Other features include internal digital soft-start, a power-good output, and a 3.5V ±1% reference output. The MAX1639 is available in a 16-pin narrow SOIC package.

### Applications

Local DC-DC Converters for CPUs

Workstations

**Desktop Computers** 

LAN Servers

**GTL Bus Termination** 

### **Ordering Information**

PART	TEMP RANGE	PIN-PACKAGE		
MAX1639ESE	40°C to +85°C	16 Narrow SO		
MAX1639ESE+	40°C to +85°C	16 Narrow SO		

+Denotes lead-free packages.

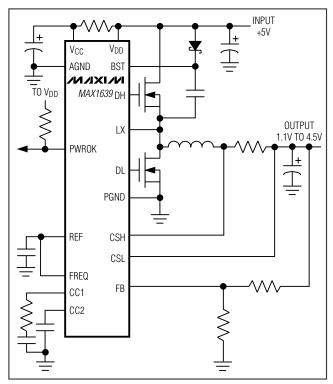
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Pin Configuration appears at end of data sheet.

### **Features**

- Better than ±1% Output Accuracy Over Line and Load
- Greater than 90% Efficiency Using N-Channel **MOSFETs**
- Pin-Selected High Switching Frequency: 300kHz, 600kHz, or 1MHz
- Over 35A Output Current
- Resistor-Divider Adjustable Output from 1.1V to 4.5V
- Current-Mode Control for Fast Transient **Response and Cycle-by-Cycle Current-Limit** Protection
- Short-Circuit Protection with Foldback Current Limiting
- Crowbar Overvoltage Protection
- Power-Good (PWROK) Output
- Digital Soft-Start
- High-Current (2A) Drive Outputs

### Typical Operating Circuit



#### Maxim Integrated Products 1

**MAX1639** 

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### **ABSOLUTE MAXIMUM RATINGS**

VDD, VCC, PWROK to AGND	
PGND to AGND	±0.3V
CSH, CSL to AGND	0.3V to (V <sub>CC</sub> + 0.3V)
DL to PGND	
REF, CC1, CC2, FREQ, FB to AGND	0.3V to (V <sub>CC</sub> + 0.3V)
BST to PGND	0.3V to +12V
BST to LX	0.3V to +6V
DH to LX(	LX - 0.3V) to (BST + 0.3V)

Continuous Power Dissipation (T <sub>A</sub> =	
16-Pin Narrow SO (derate 8.70mW/	°C above +70°C)696mW
SO ØJC	65°C/W
Operating Temperature Range	
MAX1639ESE	40°C to +85°C
Storage Temperature Range	65°C to +160°C
Lead Temperature (soldering, 10s)	+300°C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

### **ELECTRICAL CHARACTERISTICS**

(V<sub>DD</sub> = V<sub>CC</sub> = +5V, PGND = AGND = 0V, FREQ = REF, **T<sub>A</sub> = 0°C to +85°C**, unless otherwise noted.)

PARAMETER	CONDITIONS		MIN	TYP	MAX	UNITS	
	Includes line and load T		$T_A = +25^{\circ}C \text{ to } +85^{\circ}C$	1.089		1.111	V
FB Voltage	regulation e	regulation errors $T_A = 0^{\circ}C$ to $+85^{\circ}C$		1.083		1.117	
Input Voltage Range	V <sub>C</sub> C = V <sub>D</sub> D			4.5		5.5	V
Input Undervoltage Lockout	V <sub>CC</sub> rising e	dge, 1% hyste	eresis	4.0		4.2	V
	Operating		FB overdrive = 60mV			2.5	
Vec Supply Current (lec)	V <sub>CC</sub> = V <sub>DD</sub>	mode	FB overdrive = 0V		5		– mA
VCC Supply Current (ICC)	= 5.5V	Shutdown mode	V <sub>REF</sub> = 0V		3.6	10	
VDD Supply Current (IDD)			ced 60mV above or standby mode			0.1	mA
Reference Voltage	No load			3.465	3.5	3.535	V
Reference Load Regulation	0µA < IREF <	< 100µA				10	mV
Reference Undervoltage Lockout	Rising edge	, 1% hysteres	is	2.7		3.0	V
Reference Short-Circuit Current	$V_{REF} = 0V$			0.5		4.0	mA
AC Load Regulation	CSH - CSL =	= 0mV to 80m'	V		1		%
DC Load Regulation	CSH - CSL =	= 0mV to 80m'	V		0.1		%
PWROK Trip Level	Rising FB, 1% hysteresis with respect to VREF			-7.5	-6	-4.5	- %
FWROK INPLEVE	Falling FB, 1	% hysteresis	with respect to V <sub>REF</sub>	6.5	8	9.5	70
PWROK Output Voltage Low	I <sub>SINK</sub> = 2mA	$V_{\rm CC} = 4.5 V$				0.4	V
PWROK Output Current High	PWROK = 5	PWROK = 5.5V				1	μA
	FREQ = V <sub>CC</sub>		850	1000	1150	kHz	
Switching Frequency	FREQ = REF		540	600	660		
	FREQ = AGND		255	300	345		
Maximum Duty Cycle	$FREQ = V_{CC}$		85	90		%	
	GND (low)					0.2	
FREQ Input Voltage	REF (mid)			3.3		3.7	V
	Vcc (high)			Vcc - 0.1	1		]



## **ELECTRICAL CHARACTERISTICS (continued)**

 $(V_{DD} = V_{CC} = +5V, PGND = AGND = 0V, FREQ = REF, T_A = 0^{\circ}C \text{ to } +85^{\circ}C, \text{ unless otherwise noted.})$ 

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
FREQ Input Current				4	μA	
CSH, CSL Input Current	CSH = CSL = 1.1V			50	μA	
FB Input Current				±0.1	μA	
CC1 Output Resistance			10		kΩ	
CC2 Transconductance			1		mmho	
CC2 Clamp Voltage	Minimum	2.4		3.0	V	
CC2 Clamp Voltage	Maximum	4		Vcc		
CC2 Source/Sink Current	30mV overdrive		100		μA	
DH On-Resistance	BST - LX = 4.5V		0.7	2	Ω	
DL On-Resistance	$V_{DD} = 4.5V$		0.7	2	Ω	
DH, DL Source/Sink Current	DH = DL = 2.5V		2		A	
DH, DL Dead Time		0	30		ns	
	FB = 1.1V	85	100	115		
Current-Limit Trip Voltage	FB = 0V (foldback)	15	38	70	- mV	
Soft-Start Time	To full current limit		1536		1 / fosc	
BST Leakage Current	BST = 12V, LX = 7V, REF = GND			50	μA	

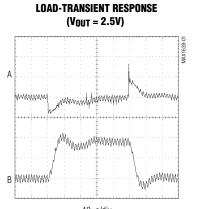
### **ELECTRICAL CHARACTERISTICS**

 $(V_{DD} = V_{CC} = +5V, PGND = AGND = 0V, FREQ = REF, T_A = -40^{\circ}C \text{ to } +85^{\circ}C, unless otherwise noted.) (Note 1)$ 

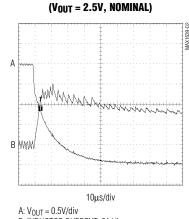
PARAMETER		CONDITIONS		MIN	TYP	MAX	UNITS
Input Voltage Range	V <sub>CC</sub> = V <sub>DD</sub>		4.5		5.5	V	
Input Undervoltage Range	V <sub>CC</sub> rising edg	ge, 1% hysteresis		3.9		4.3	V
Vaa Supply Current	V <sub>CC</sub> = V <sub>DD</sub> =	Operating mode	FB overdrive = 60mV			3	mA
V <sub>DD</sub> Supply Current	5.5V	Shutdown mode	VREF = 0V			12	
V <sub>DD</sub> Supply Current	$V_{CC} = V_{DD} = 5.5V$ , FB forced 60mV above regulation point, operating or shutdown mode					0.2	mA
Reference Voltage	No load			3.448		3.553	V
FB Voltage	Includes line and load regulation errors		1.072		1.128	V	
PWROK Trip Level	Rising FB, 1% hysteresis with respect to V <sub>REF</sub>		-8		-4	%	
FWROK INP Level	Falling FB, 1%	hysteresis with res	pect to V <sub>REF</sub>	6		10	70
	$FREQ = V_{CC}$			800		1200	
Switching Frequency	FREQ = REF			510		690	kHz
	FREQ = AGND			240		360	1
Maximum Duty Cycle	$FREQ = V_{CC}$		84			%	
DH On-Resistance	BST - LX = 4.5V				2	Ω	
DL On-Resistance	$V_{DD} = 4.5 V$				2	Ω	
Current-Limit Trip Voltage	FB = 1.1V		70		130	mV	

**Note 1:** Specifications from 0°C to -40°C are guaranteed by design, not production tested.

 $(T_A = +25^{\circ}C)$ , using the MAX1639 evaluation kit, unless otherwise noted.)



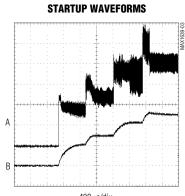
 $\begin{array}{l} 10 \mu s/div \\ V_{IN}=5V, V_{0UT}=2.5V, \ LOAD=8A \\ A: \ V_{0UT}, \ 100 mV/div, \ AC \ COUPLED \\ B: \ INDUCTOR \ CURRENT, \ 5A/div \end{array}$ 



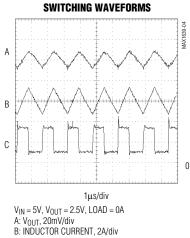
FOLDBACK CURRENT LIMIT

B: INDUCTOR CURRENT, 5A/div

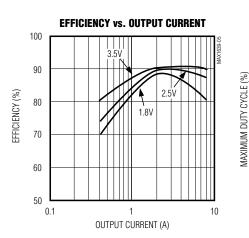
**Typical Operating Characteristics** 



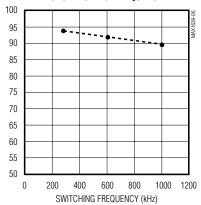
 $\begin{array}{l} 400 \mu s/div \\ \text{A: INDUCTOR CURRENT, 2A/div} \\ \text{B: V}_{\text{OUT}} = 1V/div \end{array}$ 



C: LX, 5V/div



MAXIMUM DUTY CYCLE vs. Switching Frequency



# Pin Description

PIN	NAME	FUNCTION
FIN		
1	BST	Boost-Capacitor Bypass for High-Side MOSFET Gate Drive. Connect a 0.1µF capacitor and low-leak- age Schottky diode as a bootstrapped charge-pump circuit to derive a 5V gate drive from V <sub>DD</sub> for DH.
2	PWROK	Open-Drain Logic Output. PWROK is high when the voltage on FB is within +8% and -6% of its set- point.
3	CSL	Current-Sense Amplifier's Inverting Input. Place the current-sense resistor very close to the controller IC, and use a Kelvin connection.
4	CSH	Current-Sense Amplifier's Noninverting Input
5	Vcc	Analog Supply Input, 5V. Use an RC filter network, as shown in Figure 1.
6	REF	Reference Output, 3.5V. Bypass REF to AGND with 0.1µF (min). Sources up to 100µA for external loads. Force REF below 2V to turn off the controller.
7	AGND	Analog Ground
8	FB	Voltage-Feedback Input. The voltage at this input is regulated to 1.100V.
9	CC1	Fast-Loop Compensation Capacitor Input. Connect a ceramic capacitor and resistor in series from CC1 to AGND. See the section <i>Compensating the Feedback Loop</i> .
10	CC2	Slow-Loop Compensation Capacitor Input. Connect a ceramic capacitor from CC2 to AGND. See the section <i>Compensating the Feedback Loop</i> .
11	FREQ	Frequency-Select Input. FREQ = V <sub>CC</sub> : 1MHz FREQ = REF: 600kHz FREQ = AGND: 300kHz
12	VDD	Power Input for MOSFET Drivers, 5V. Bypass $V_{DD}$ to PGND within 0.2 in. (5mm) of the $V_{DD}$ pin using a 0.1µF capacitor and 4.7µF capacitor connected in parallel.
13	DL	Low-Side Synchronous Rectifier Gate-Drive Output. DL swings between PGND and V <sub>DD</sub> . See the section <i>BST High-Side Gate-Driver Supply and MOSFET Drivers</i> .
14	PGND	Power Ground
15	LX	Switching Node. Connect LX to the high-side MOSFET source and inductor.
16	DH	High-Side Main MOSFET Switch Gate-Drive Output. DH is a floating driver output that swings from LX to BST, riding on the LX switching-node voltage. See the section <i>BST High-Side Gate-Driver Supply and MOSFET Drivers</i> .

### Standard Application Circuits

The predesigned MAX1639 circuit shown in Figure 1 meets a wide range of applications with output currents up to 35A. Use Table 1 to select components appropriate for the desired output current range, and adapt the evaluation kit PC board layout as necessary. This circuit represents a good set of trade-offs between cost, size, and efficiency while staying within the worst-case specification limits for stress-related parameters, such as capacitor ripple current.

The MAX1639 circuit was designed for the specified frequencies. Do not change the switching frequency without first recalculating component values—particularly the inductance, output filter capacitance, and RC1 resistance values.

### **Detailed Description**

The MAX1639 is a BiCMOS power-supply controller designed for use in switch-mode, step-down (buck) topology DC-DC converters. Synchronous rectification provides high efficiency. It is intended to provide the high precision, low noise, excellent transient response, and high efficiency required in today's most demanding applications.

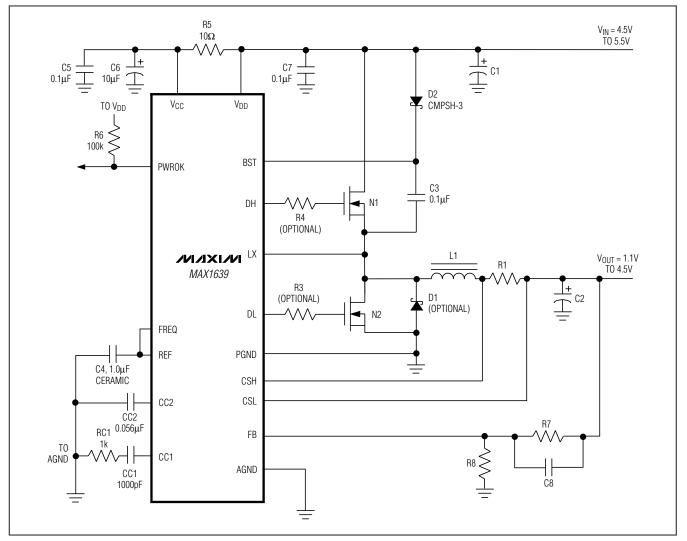


Figure 1. Standard Application Circuit

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### **Table 1. Component List for Standard Applications**

COMPONENT	LOAD REQUIREMENT			
COMPONENT	2.5V, 8A	1.8V, 20A		
C1	330µF, Sanyo OS-CON 6SA330M	(x3) 330µF, Sanyo OS-CON 6SA330M		
C2	(x2) 560µF, Sanyo OS-CON 4SP560M	(x5) 560µF, Sanyo OS-CON 4SP560M		
D1 (optional)	Schottky diode, Nihon NSQ03A02	Schottky diode, Motorola MBRD640		
D2	Central Semiconductor CMPSH-3	Central Semiconductor CMPSH-3		
L1	<b>1.0μH, 9.3A, SMD</b> <b>Coiltronics UP2B-1R0</b> 1.0μH, 10A, SMD Coilcraft D03316P-102HC	0.3μH, 25A, 0.9mΩ Panasonic ETQPAF0R3E		
0.014Ω, 30V, SO8   Fairchild FDS6680   0.018Ω, 30V, SO8   International Rectifier IRF7413		(x2) 0.010Ω, 30V, D <sup>2</sup> PAK, Fairchild FDB703 (x2) 0.014Ω, 30V, SO8, Fairchild FDS6680		
N2	0.014Ω, 30V, SO8 Fairchild FDS6680 0.018Ω, 30V, SO8 International Rectifier IRF7413	(x2) 0.010Ω, 30V, D <sup>2</sup> PAK, Fairchild FDB703 (x2) 0.014Ω, 30V, SO8, Fairchild FDS6680		
R1	9mΩ Dale, WSL-2512-R009-J	(x2) 7mΩ, Dale WSL-2512-R007-J		
R7	<b>10.0k</b> Ω, <b>1%</b>	10.0kΩ, 1%		
R8	<b>12.7k</b> Ω, <b>1%</b>	6.19kΩ, 1%		

Note: Parts used in evaluation board are shown in bold.

### **PWM Controller Block and Integrator**

The heart of the current-mode PWM controller is a multi-input, open-loop comparator that sums three signals (Figure 2): the buffered feedback signal, the current-sense signal, and the slope-compensation ramp. This direct-summing configuration approaches ideal cycle-by-cycle control over the output voltage. The output voltage error signal is generated by an error amplifier that compares the amplified feedback voltage to an internal reference.

Each pulse from the oscillator sets the main PWM latch that turns on the high-side switch for a period determined by the duty factor (approximately VOUT / VIN). The current-mode feedback system regulates the peak inductor current as a function of the output voltage error signal. Since average inductor current is nearly the same as peak current (assuming the inductor value is set relatively high to minimize ripple current), the circuit acts as a switch-mode transconductance amplifier. It pushes the second output LC filter pole, normally found in a dutyfactor-controlled (voltage-mode) PWM, to a higher frequency. To preserve inner-loop stability and eliminate regenerative inductor current staircasing, a slopecompensation ramp is summed into the main PWM comparator. Under fault conditions where the inductor current exceeds the maximum current-limit threshold, the high-side latch resets, and the high-side switch turns off.

### 

### **Internal Reference**

The internal 3.5V reference (REF) is accurate to  $\pm 1\%$  from 0°C to +85°C, making REF useful as a system reference. Bypass REF to AGND with a 0.1µF (min) ceramic capacitor. A larger value (such as 2.2µF) is recommended for high-current applications. Load regulation is 10mV for loads up to 100µA. Reference undervoltage lockout is between 2.7V and 3V. Short-circuit current is less than 4mA.

#### **Synchronous-Rectifier Driver**

Synchronous rectification reduces conduction losses in the rectifier by shunting the normal Schottky diode or MOSFET body diode with a low-on-resistance MOSFET switch. The synchronous rectifier also ensures proper start-up by precharging the boost-charge pump used for the high-side switch gate-drive circuit. Thus, if you must omit the synchronous power MOSFET for cost or other reasons, replace it with a small-signal MOSFET, such as a 2N7002.

The DL drive waveform is simply the complement of the DH high-side drive waveform (with typical controlled dead time of 30ns to prevent cross-conduction or shoot-through). The DL output's on-resistance is  $0.7\Omega$  (typ) and  $2\Omega$  (max).



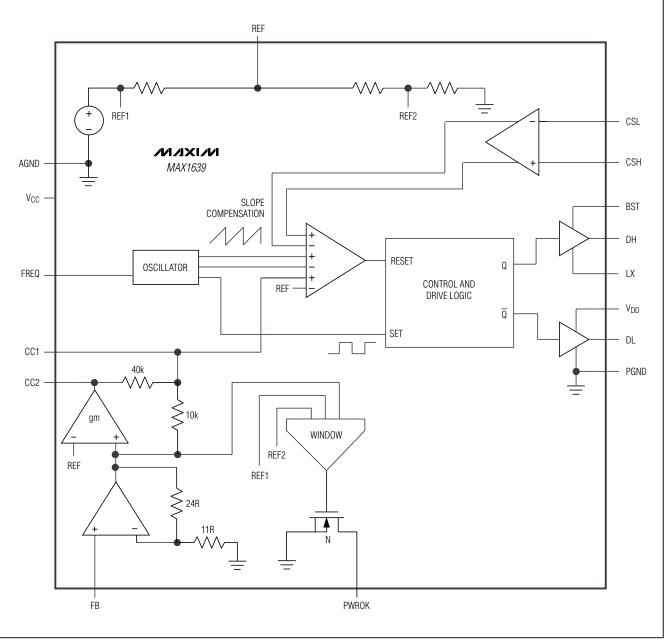


Figure 2. Simplified Block Diagram

### **BST High-Side Gate-Driver Supply** and MOSFET Drivers

Gate-drive voltage for the high-side N-channel switch is generated using a flying-capacitor boost circuit (Figure 3). The capacitor is alternately charged from the +5V supply and placed in parallel with the highside MOSFET's gate and source terminals.

Gate-drive resistors (R3 and R4) can often be useful to reduce jitter in the switching waveforms by slowing down the fast-slewing LX node and reducing ground bounce at the controller IC. However, switching loss may increase. Low-value resistors from around  $1\Omega$  to  $5\Omega$  are sufficient for many applications.

### **Current Sense** and Overload Current Limiting

The current-sense circuit resets the main PWM latch and turns off the high-side MOSFET switch whenever the voltage difference between CSH and CSL from current through the sense resistor (R1) exceeds the peak current limit (100mV typical).

Current-mode control provides cycle-by-cycle currentlimit capability for maximum overload protection. During normal operation, the peak current limit set by the current-sense resistor determines the maximum output current. When the output is shorted, the peak current may be higher than the set current limit due to delays in the current-sense comparator. Thus, foldback current limiting is employed where the set current-limit point is reduced from 100mV to 38mV as the output (feedback) voltage falls (Figure 4). When the shortcircuit condition is removed, the feedback voltage will rise and the current-limit voltage will revert to 100mV. The foldback current-limit circuit is designed to ensure startup into a resistive load.

### **High-Side Current Sensing**

The common-mode input range of the current-sense inputs (CSH and CSL) extends to V<sub>CC</sub>, so it is possible to configure the circuit with the current-sense resistor on the input side rather than on the load side (Figure 5). This configuration improves efficiency by reducing the power dissipation in the sense resistor according to the duty ratio.

In the high-side configuration, if the output is shorted directly to GND through a low-resistance path, the current-sense comparator may be unable to enforce a current limit. Under such conditions, circuit parasitics such as MOSFET RDS(ON) typically limit the shortcircuit current to a value around the peak-currentlimit setting.

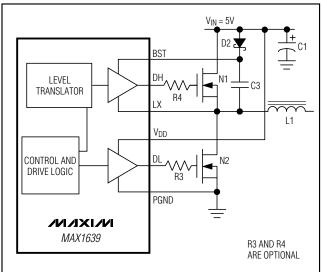


Figure 3. Boost Supply for Gate Drivers

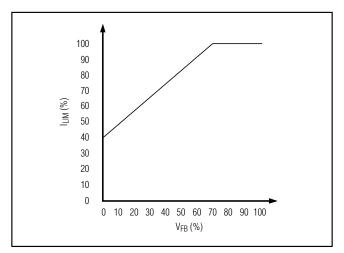


Figure 4. Foldback Current Limit

Attach a lowpass-filter network between the currentsense pins and resistor to reduce high-frequency common-mode noise. The filter should be designed with a time constant of around one-fifth of the on-time (130ns at 600kHz, for example). Resistors in the  $20\Omega$  to  $100\Omega$  range are recommended for R9 and R10. Connect the filter capacitors C9 and C10 from V<sub>CC</sub> to CSH and CSL, respectively.

Values of  $39\Omega$  and 3.3nF are suitable for many designs. Place the current-sense filter network close to the IC, within 0.1 in (2.5mm) of the CSH and CSL pins.

**MAX1639** 

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### **Overvoltage Protection**

When the output exceeds the set voltage, the synchronous rectifier output (DL) is driven high (and DH is driven low). This causes the inductor to quickly dissipate any stored energy and force the fault current to flow to ground. Current is limited by the source impedance and parasitic resistance of the current path, so a fuse is required in series with the +5V input to protect against low-impedance faults, such as a shorted high-side MOSFET. Otherwise, the low-side MOSFET will eventually fail. DL will go low if the input voltage drops below the undervoltage lockout point.

#### **Internal Soft-Start**

Soft-start allows a gradual increase of the internal current limit at start-up to reduce input surge currents. An internal DAC raises the current-limit threshold from 0V to 100mV in four steps (25mV, 50mV, 75mV, and 100mV) over the span of 1536 oscillator cycles.

### \_Design Procedure

### Setting the Output Voltage

Set the output voltage by connecting R7 and R8 (Figure 6) to the FB pin from the output to AGND. R7 is given by the following equation:

$$R7 = R8 x \left(\frac{V_{OUT}}{V_{FB}} - 1\right)$$

where V<sub>FB</sub> = 1.1V. Since the input bias current at FB has a maximum value of  $\pm 0.1 \mu$ A, values up to  $10 k\Omega$  can be used for R8 with no significant accuracy loss.

Values under  $1k\Omega$  are recommended to improve noise immunity. Place R7 and R8 very close to the MAX1639, within 0.2in (5mm) of the FB pin.

#### Feed-Forward Compensation

An optional compensation capacitor ( $\overline{C8}$ ), typically 220pF, may be needed across the upper feedback resistor to counter the effects of stray capacitance on the FB pin, and to help ensure stable operation when high-value feedback resistors are used (Figure 6). Empirically adjust the feed-forward capacitor as needed.

### **Specifying the Inductor**

Three key inductor parameters must be specified: inductance value (L), peak current ( $I_{PEAK}$ ), and DC resistance ( $R_{DC}$ ). The following equation includes a constant LIR, which is the ratio of inductor peak-topeak AC current to DC load current. Typically LIR can be between 0.1 to 0.5. A higher LIR value allows for smaller inductors and better transient response, but

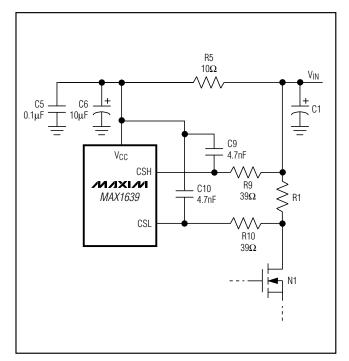


Figure 5. High-Side Current Sense

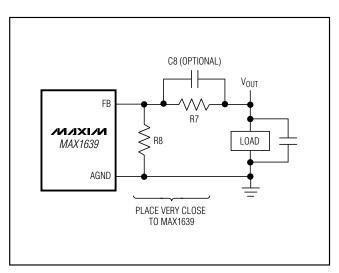


Figure 6. Output Selection

results in higher losses and output ripple. A good compromise between size and loss is a 30% ripple current to load current ratio (LIR = 0.30), which corresponds to a peak inductor current 1.15 times higher than the DC load current.



$$L = \frac{V_{OUT} (V_{IN(MAX)} - V_{OUT})}{V_{IN(MAX)} \times f_{OSC} \times I_{OUT} \times LIR}$$

where f is the switching frequency, between 300kHz and 1MHz;  $I_{OUT}$  is the maximum DC load current; and LIR is the ratio of AC to DC inductor current (typically 0.3). The exact inductor value is not critical and can be adjusted to make trade-offs among size, transient response, cost, and efficiency. Although lower inductor values minimize size and cost, they also reduce efficiency due to higher peak currents. In general, higher inductor values increase efficiency, but at some point resistive losses due to extra turns of wire exceed the benefit gained from lower AC current levels. Load-transient response can be adversely affected by high inductor values, especially at low (V<sub>IN</sub> - V<sub>OUT</sub>) differentials.

The peak inductor current at full load is  $1.15 \times I_{OUT}$  if the previous equation is used; otherwise, the peak current can be calculated using the following equation:

$$I_{PEAK} = I_{OUT} + \frac{V_{OUT} \left( V_{IN(MAX)} - V_{OUT} \right)}{2f_{OSC} \times L \times V_{IN(MAX)}}$$

The inductor's DC resistance is a key parameter for efficient performance, and should be less than the currentsense resistor value.

#### Calculating the Current-Sense Resistor Value

Calculate the current-sense resistor value according to the worst-case minimum current-limit threshold voltage (from the *Electrical Characteristics*) and the peak inductor current required to service the maximum load. Use IPEAK from the equation in the section *Specifying the Inductor*.

$$R_{SENSE} = \frac{85mV}{I_{PEAK}}$$

The high inductance of standard wire-wound resistors can degrade performance. Low-inductance resistors, such as surface-mount power metal-strip resistors, are preferred. The current-sense resistor's power rating should be higher than the following:

In high-current applications, connect several resistors in parallel as necessary to obtain the desired resistance and power rating.

Selecting the Output Filter Capacitor Output filter capacitor values are generally determined by effective series resistance (ESR) and voltage-rating requirements, rather than by the actual capacitance value required for loop stability. Due to the high switching currents and demanding regulation requirements in a typical MAX1639 application, use only specialized low-ESR capacitors intended for switchingregulator applications, such as AVX TPS, Kemet T510, Sprague 595D, Sanyo OS-CON, or Sanyo GX series. Do not use standard aluminum-electrolytic capacitors. which can cause high output ripple and instability due to high ESR. The output voltage ripple is usually dominated by the filter capacitor's ESR, and can be approximated as IRIPPLE x RESR. To ensure stability, the capacitor must meet both minimum capacitance and maximum ESR values as given in the following equations:

$$C_{OUT} > \frac{V_{REF} \left(1 + \frac{V_{OUT}}{V_{IN(MIN)}}\right)}{V_{OUT} \times R_{SENSE} \times f_{OSC}}$$

 $R_{ESR} < R_{SENSE}$ 

#### **Compensating the Feedback Loop**

The feedback loop needs proper compensation to prevent excessive output ripple and poor efficiency caused by instability. Compensation cancels unwanted poles and zeros in the DC-DC converter's transfer function that are due to the power-switching and filter elements with corresponding zeros and poles in the feedback network. These compensation zeros and poles are set by the compensation components CC1, CC2, and RC1. The objective of compensation is to ensure stability by ensuring that the DC-DC converter's phase shift is less than 180° by a safe margin, at the frequency where the loop gain falls below unity.

#### Canceling the Sampling Pole and Output Filter ESR Zero

Compensate the fast-voltage feedback loop by connecting a resistor and a capacitor in series from the CC1 pin to AGND. The pole from CC1 can be set to cancel the zero from the filter-capacitor ESR. Thus the capacitor at CC1 should be as follows:

M/XI/M

$$CC1 = \frac{C_{OUT} \times R_{ESR}}{10k\Omega}$$

Resistor RC1 sets a zero that can be used to compensate for the sampling pole generated by the switching frequency. Set RC1 to the following:

$$RC1 = \frac{\left(1 + \frac{V_{OUT}}{V_{IN}}\right)}{2f_{OSC} \times CC1}$$

The CC1 pin's output resistance is  $10k\Omega$ .

#### Setting the Dominant Pole and Canceling the Load and Output Filter Pole

Compensate the slow-voltage feedback loop by adding a ceramic capacitor from the CC2 pin to AGND. This is an integrator loop used to cancel out the DC loadregulation error. Selection of capacitor CC2 sets the dominant pole and a compensation zero. The zero is typically used to cancel the unwanted pole generated by the load and output filter capacitor at the maximum load current. Select CC2 to place the zero close to or slightly lower than the frequency of the unwanted pole, as follows:

$$CC2 = \frac{1mmho \times C_{OUT}}{4} \times \frac{V_{OUT}}{I_{OUT(MAX)}}$$

The transconductance of the integrator amplifier at CC2 is 1mmho. The voltage swing at CC2 is internally clamped around 2.4V to 3V minimum and 4V to V<sub>CC</sub> maximum to improve transient response times. CC2 can source and sink up to  $100\mu$ A.

#### **Choosing the MOSFET Switches**

The two high-current N-channel MOSFETs must be logic-level types with guaranteed on-resistance specifications at  $V_{GS}$  = 4.5V. Lower gate-threshold specs are better (i.e., 2V max rather than 3V max). Gate charge should be less than 200nC to minimize switching losses and reduce power dissipation.

I<sup>2</sup>R losses are the greatest heat contributor to MOSFET power dissipation and are distributed between the high- and low-side MOSFETs according to duty factor, as follows:

$$P_D$$
 (high side) =  $I_{LOAD}^2 \times R_{DS(ON)} \times \frac{V_{OUT}}{V_{IN}}$ 

$$P_D$$
 (low side) =  $I_{LOAD}^2 \times R_{DS(ON)} \times \left(1 - \frac{V_{OUT}}{V_{IN}}\right)$ 

Gate-charge losses are dissipated in the IC, and do not heat the MOSFETs. Ensure that both MOSFETs are at a safe junction temperature by calculating the temperature rise according to package thermal-resistance specifications. The high-side MOSFET's worst-case dissipation occurs at the maximum output voltage and minimum input voltage. For the low-side MOSFET, the worst case is at the maximum input voltage when the output is shortcircuited (consider the duty factor to be 100%).

#### **Calculating IC Power Dissipation**

Power dissipation in the IC is dominated by average gate-charge current into both MOSFETs. Average current is approximately:

$$I_{DD} = (Q_{G1} + Q_{G2}) \times f_{OSC}$$

where  $\mathsf{I}_{DD}$  is the drive current,  $\mathsf{Q}_G$  is the total gate charge for each MOSFET, and  $\mathsf{f}_{OSC}$  is the switching frequency.

Power dissipation of the IC is:

 $P_D = I_{CC} \times V_{CC} + I_{DD} \times V_{DD}$ 

where ICC is the quiescent supply current of the IC.

Junction temperature for the IC is primarily a function of the PC board layout, since most of the heat is removed through the traces connected to the pins and the ground and power planes. A 16-pin narrow SO on a typical four-layer board with ground and power planes show equivalent junction-to-ambient thermal impedance of ( $\theta_{JA}$ ) about 80°C/W. Junction temperature of the die is approximately:

$$T_J = P_D \times \theta_{JA} + T_A$$

where  $T_A$  is the ambient temperature.

#### **Selecting the Rectifier Diode**

The rectifier diode D1 is a clamp that catches the negative inductor swing during the 30ns typical dead time between turning off the high-side MOSFET and turning on the low-side MOSFET synchronous rectifier. D1 must be a Schottky diode, to prevent the MOSFET body diode from conducting. It is acceptable to omit D1 and let the body diode clamp the negative inductor swing, but efficiency will drop about 1%. Use a 1N5819 diode for loads up to 3A, or a 1N5822 for loads up to 10A.

#### Adding the BST Supply Diode and Capacitor

A signal diode, such as a 1N4148, works well for D2 in most applications, although a low-leakage Schottky diode provides slightly improved efficiency. Do not use

